

Abstract of the Disclosure:

In an integrated circuit configuration, above a first conductive structure which is embedded in a first insulating layer there are arranged a first barrier layer and a second insulating layer, in which a contact hole is provided which reaches down to the first conductive structure. Above the first barrier layer, the side walls of the contact hole are provided with spacers which act as a diffusion barrier and which reach down to the surface of the first barrier layer. A second conductive structure is arranged in the contact hole. The second conductive structure is conductively connected to the first conductive structure. During the production of the contact hole, the spacers prevent deposition of material from the first conductive structure on the surface of the second insulating layer.